

DATA SHEET

BFS25A
NPN 5 GHz wideband transistor

Product specification

December 1997



NPN 5 GHz wideband transistor

BFS25A

FEATURES

- Low current consumption
- Low noise figure
- Gold metallization ensures excellent reliability
- SOT323 envelope.

PINNING

PIN	DESCRIPTION
Code: N6	
1	base
2	emitter
3	collector

DESCRIPTION

NPN transistor in a plastic SOT323 envelope.

It is designed for use in RF amplifiers and oscillators in pagers and pocket phones with signal frequencies up to 2 GHz.

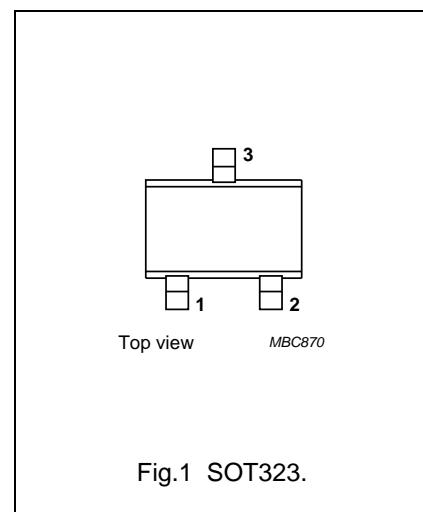


Fig.1 SOT323.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	8	V
V_{CEO}	collector-emitter voltage	open base	–	–	5	V
I_C	DC collector current		–	–	6.5	mA
P_{tot}	total power dissipation	up to $T_s = 170$ °C; note 1	–	–	32	mW
h_{FE}	DC current gain	$I_C = 0.5$ mA; $V_{CE} = 1$ V; $T_j = 25$ °C	50	80	200	
f_T	transition frequency	$I_C = 1$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	3.5	5	–	GHz
G_{UM}	maximum unilateral power gain	$I_c = 0.5$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	–	13	–	dB
F	noise figure	$I_c = 0.5$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	–	1.8	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	8	V
V_{CEO}	collector-emitter voltage	open base	–	5	V
V_{EBO}	emitter-base voltage	open collector	–	2	V
I_C	DC collector current		–	6.5	mA
P_{tot}	total power dissipation	up to $T_s = 170$ °C; note 1	–	32	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	175	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

NPN 5 GHz wideband transistor

BFS25A

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 170$ °C; note 1	190 K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

 $T_j = 25$ °C, unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 5$ V	–	–	50	nA
h_{FE}	DC current gain	$I_C = 0.5$ mA; $V_{CE} = 1$ V	50	80	200	
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 1$ V; $f = 1$ MHz	–	0.3	0.45	pF
f_T	transition frequency	$I_C = 1$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	3.5	5	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	$I_C = 0.5$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	–	13	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 0.5$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	–	1.8	–	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 1$ mA; $V_{CE} = 1$ V; $f = 1$ GHz; $T_{amb} = 25$ °C	–	2	–	dB

Note

- G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ dB.}$$

NPN 5 GHz wideband transistor

BFS25A

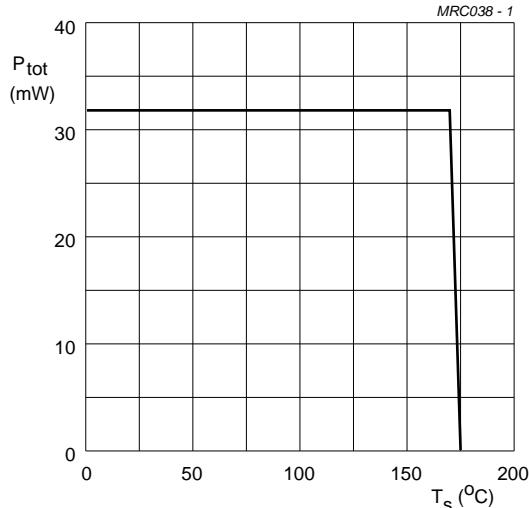


Fig.2 Power derating curve.

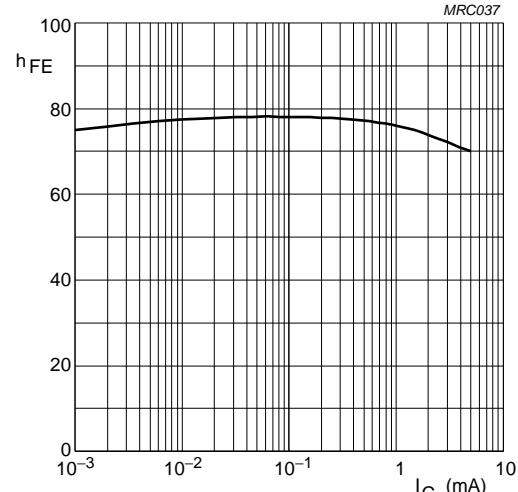
 $V_{CE} = 1$ V; $T_j = 25$ $^{\circ}$ C.

Fig.3 DC current gain as a function of collector current.

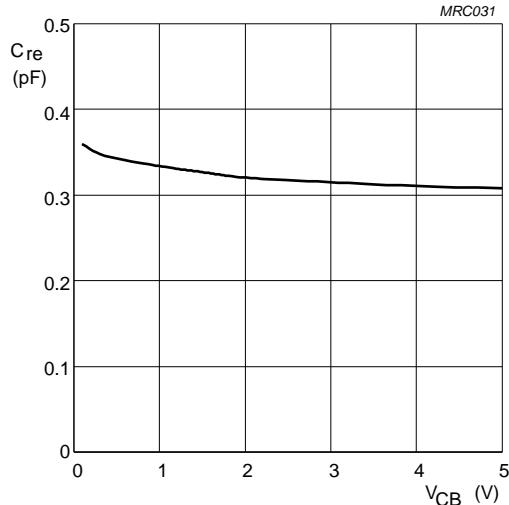
 $I_C = 0$; $f = 1$ MHz.

Fig.4 Feedback capacitance as a function of collector-base voltage.

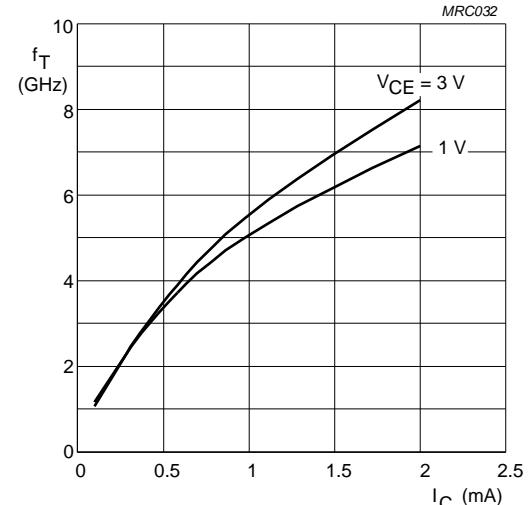
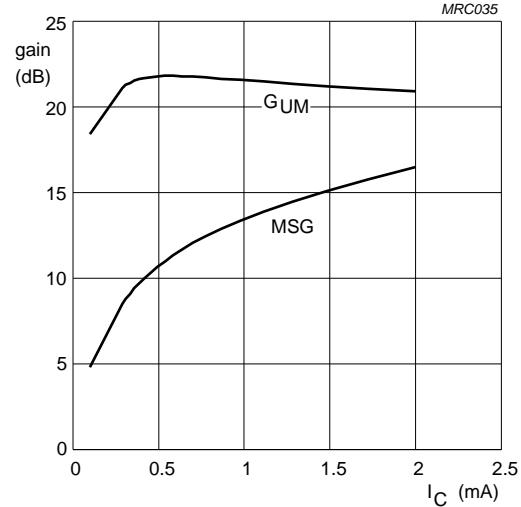
 $f = 1$ GHz; $T_{amb} = 25$ $^{\circ}$ C.

Fig.5 Transition frequency as a function of collector current.

NPN 5 GHz wideband transistor

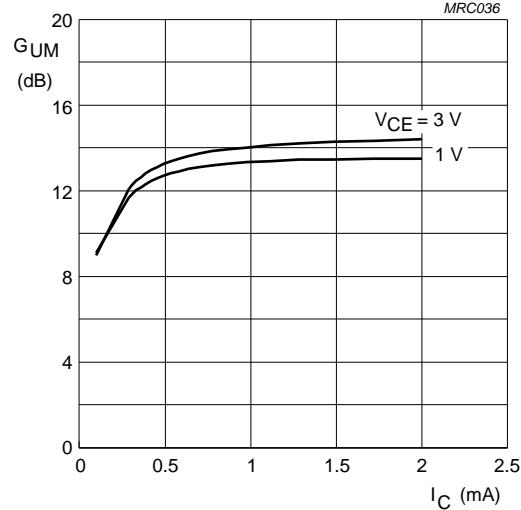
BFS25A

In Figs 7 to 9, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



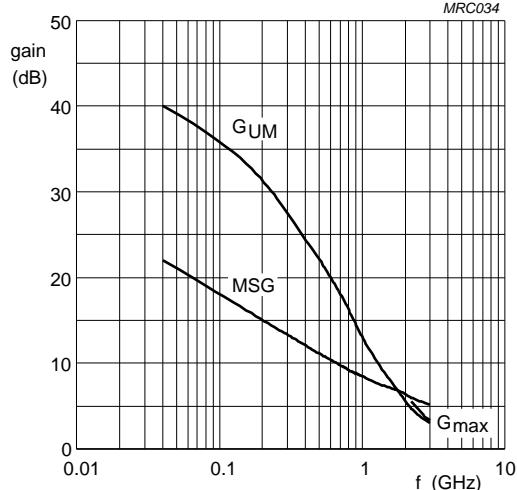
$V_{CE} = 1$ V; $f = 500$ MHz; $T_{amb} = 25$ °C.

Fig.6 Gain as a function of collector current.



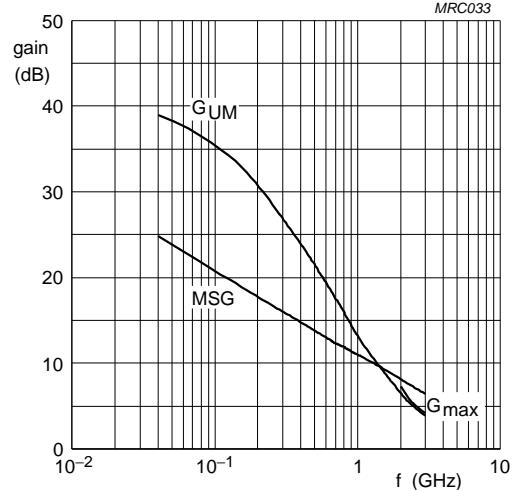
$f = 1$ GHz; $T_{amb} = 25$ °C.

Fig.7 Maximum unilateral power gain as a function of collector current.



$I_C = 0.5$ mA; $V_{CE} = 1$ V; $T_{amb} = 25$ °C.

Fig.8 Gain as a function of frequency.

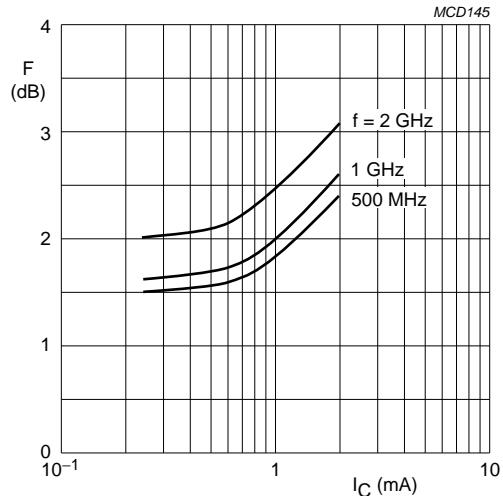


$I_C = 1$ mA; $V_{CE} = 1$ V; $T_{amb} = 25$ °C.

Fig.9 Gain as a function of frequency.

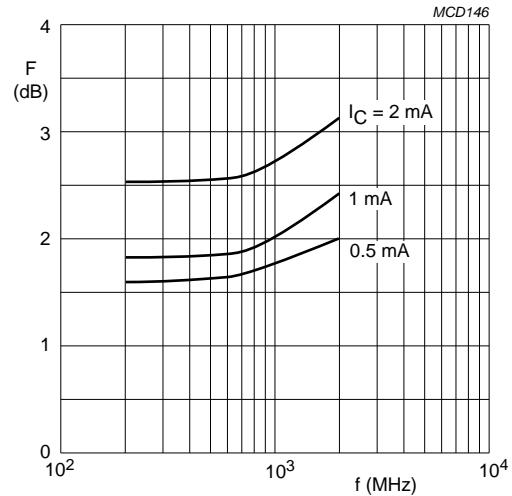
NPN 5 GHz wideband transistor

BFS25A



$V_{CE} = 1 \text{ V}; T_{amb} = 25^\circ\text{C}.$

Fig.10 Minimum noise figure as a function of collector current.



$V_{CE} = 1 \text{ V}; T_{amb} = 25^\circ\text{C}.$

Fig.11 Minimum noise figure as a function of frequency.

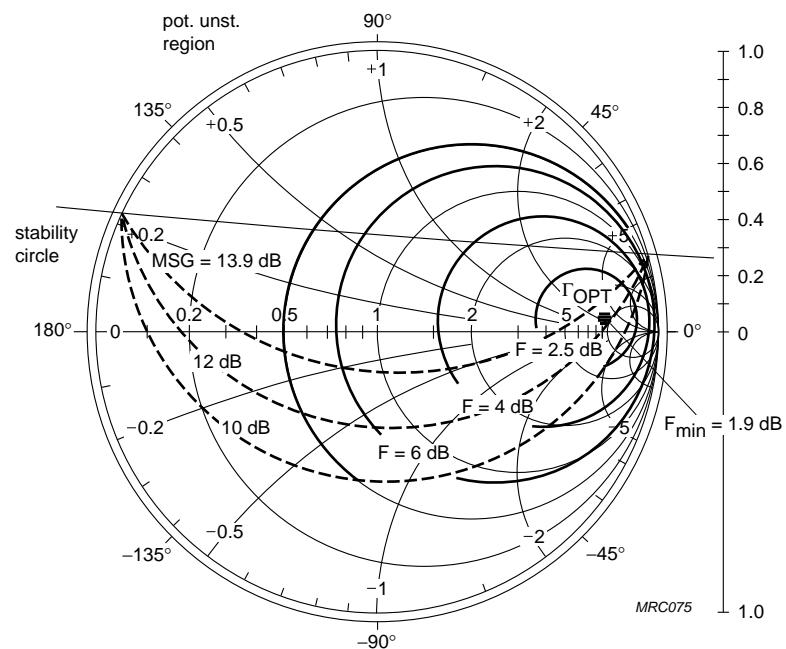
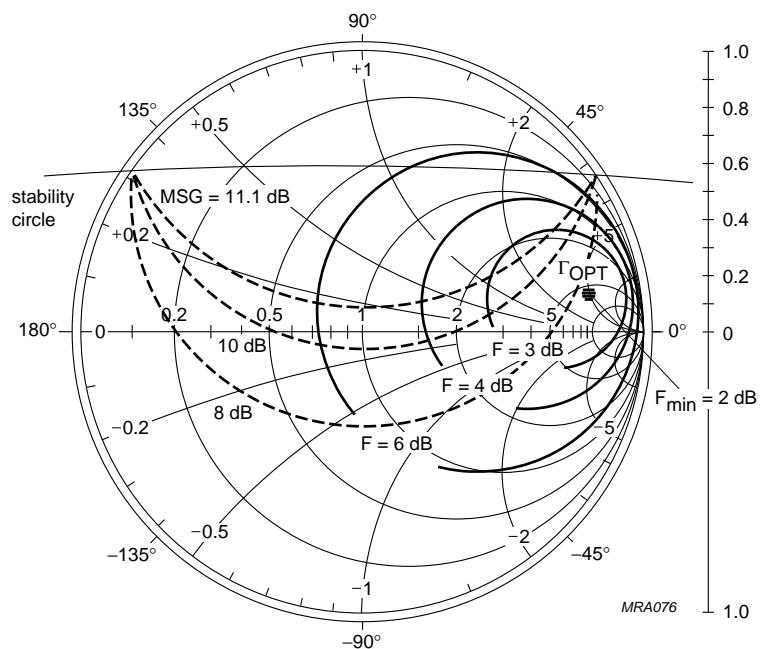


Fig.12 Noise circle.

NPN 5 GHz wideband transistor

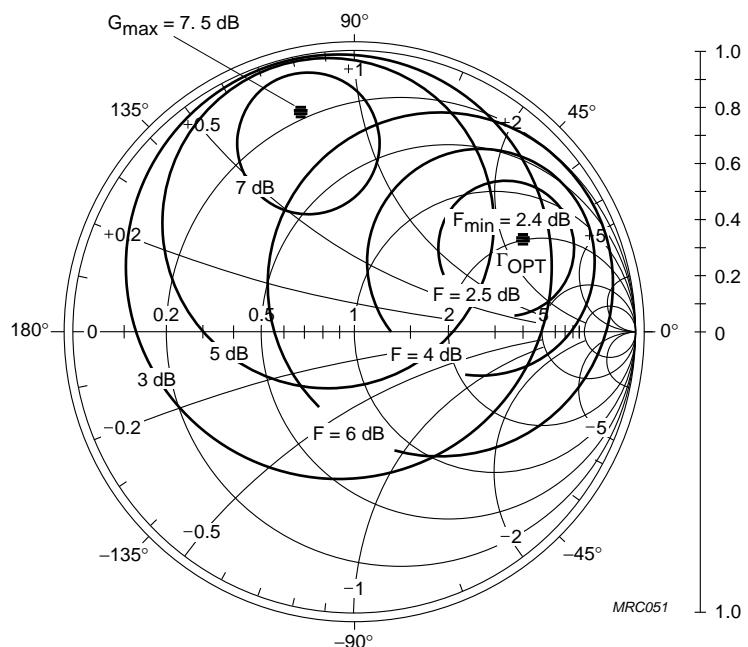
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$$I_C = 1 \text{ mA}; V_{CE} = 1 \text{ V};$$

$$f = 1 \text{ GHz}; Z_0 = 50 \Omega.$$

Fig.13 Noise circle.



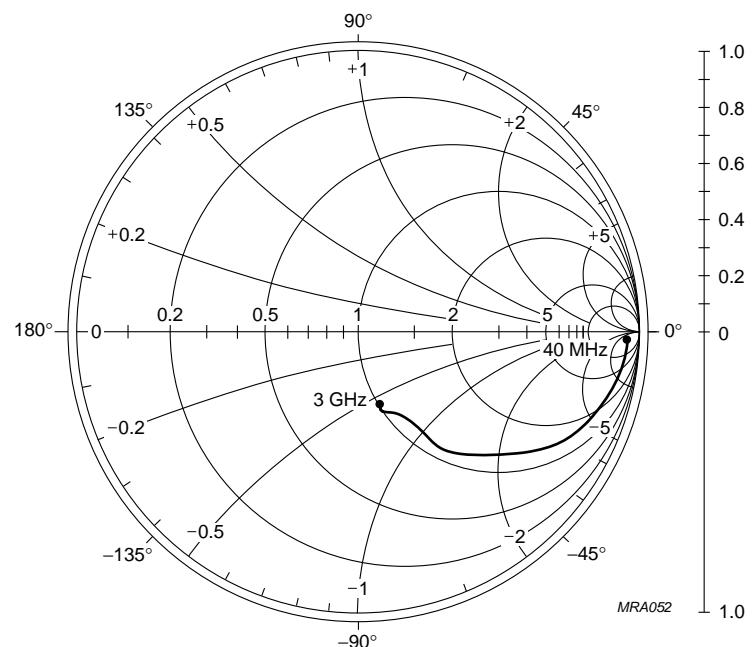
$$I_C = 1 \text{ mA}; V_{CE} = 1 \text{ V};$$

$$f = 2 \text{ GHz}; Z_o = 50 \Omega.$$

Fig.14 Noise circle.

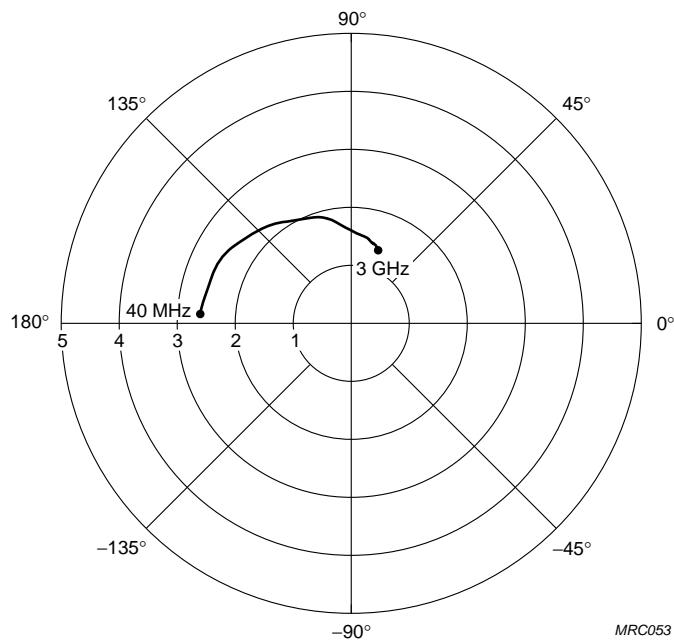
NPN 5 GHz wideband transistor

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$I_C = 1 \text{ mA}$; $V_{CE} = 1 \text{ V}$;
 $Z_0 = 50 \Omega$.

Fig.15 Common emitter input reflection coefficient (S_{11}).

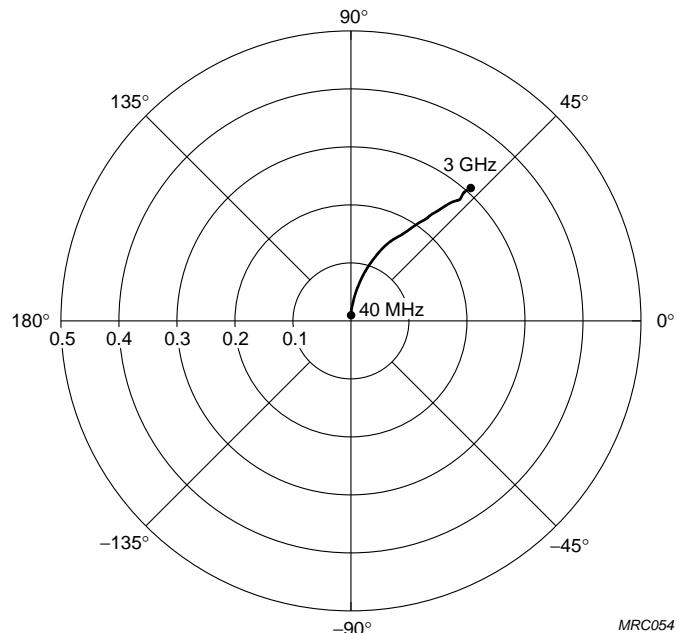
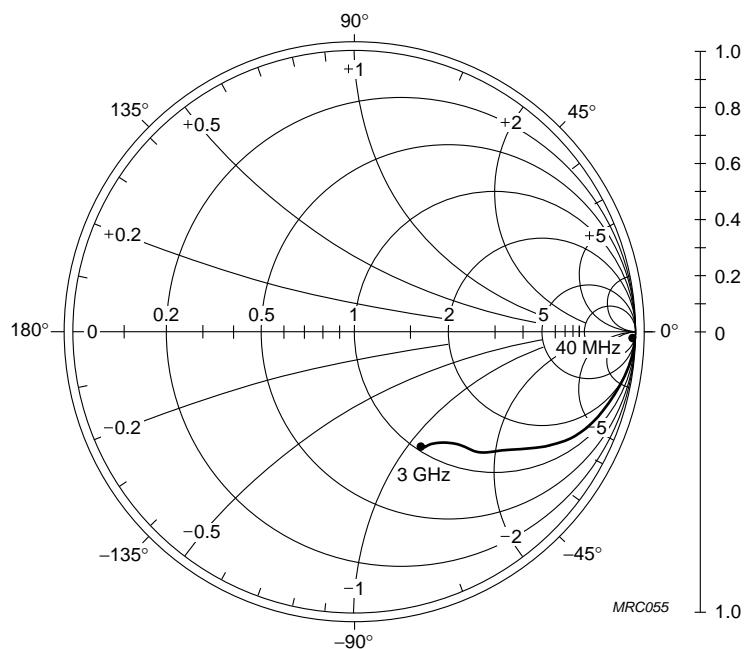


$I_C = 1 \text{ mA}$; $V_{CE} = 1 \text{ V}$.

Fig.16 Common emitter forward transmission coefficient (S_{21}).

NPN 5 GHz wideband transistor

BFS25A

 $I_C = 1 \text{ mA}; V_{CE} = 1 \text{ V}.$ Fig.17 Common emitter reverse transmission coefficient (S_{12}). $I_C = 1 \text{ mA}; V_{CE} = 1 \text{ V};$
 $Z_0 = 50 \Omega.$ Fig.18 Common emitter output reflection coefficient (S_{22}).

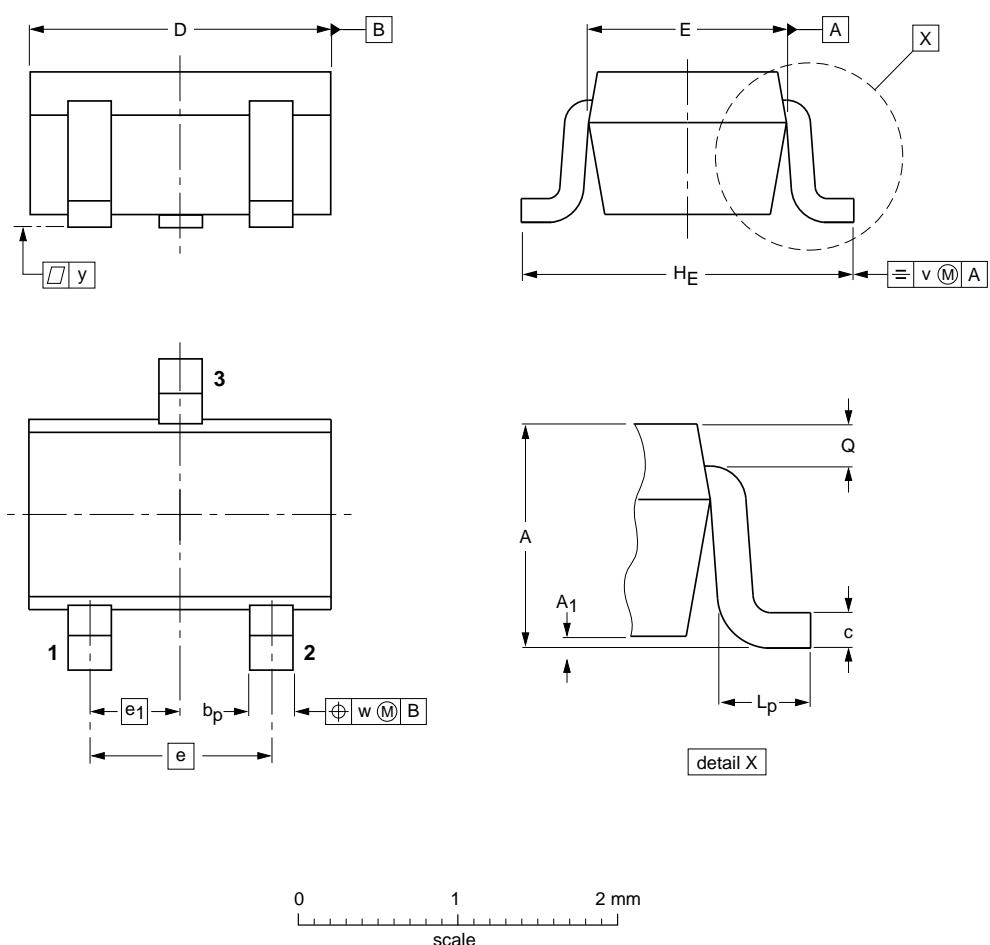
NPN 5 GHz wideband transistor

BFS25A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA	SC-70		
SOT323						-04-11-04- 06-03-16

NPN 5 GHz wideband transistor

BFS25A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NPN 5 GHz wideband transistor

BFS25A

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